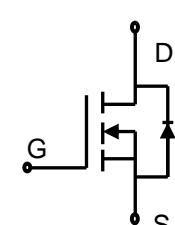


## Lonten P-channel -20V, -2A, 110mΩ Power MOSFET

<p><b>Description</b></p> <p>These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.</p>	<p><b>Product Summary</b></p> <table border="0"> <tr> <td><math>V_{DSS}</math></td><td>-20V</td></tr> <tr> <td><math>R_{DS(on).max} @ V_{GS}=-4.5V</math></td><td>110mΩ</td></tr> <tr> <td><math>I_D</math></td><td>-2A</td></tr> </table>	$V_{DSS}$	-20V	$R_{DS(on).max} @ V_{GS}=-4.5V$	110mΩ	$I_D$	-2A
$V_{DSS}$	-20V						
$R_{DS(on).max} @ V_{GS}=-4.5V$	110mΩ						
$I_D$	-2A						
<p><b>Features</b></p> <ul style="list-style-type: none"> <li>◆ -20V, -2A, <math>R_{DS(ON).max}=110m\Omega @ V_{GS}=-4.5V</math></li> <li>◆ Improved dv/dt capability</li> <li>◆ Fast switching</li> <li>◆ Green device available</li> </ul> <p><b>Applications</b></p> <ul style="list-style-type: none"> <li>◆ PWM applications</li> <li>◆ Load switch</li> <li>◆ Portable Equipment</li> </ul>	<p><b>Pin Configuration</b></p>  <p><b>SOT-23</b></p>  <p>P-Channel MOSFET</p> 						

### Absolute Maximum Ratings $T_A = 25^\circ C$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-20	V
Continuous drain current ( $T_A = 25^\circ C$ )	$I_D$	-2	A
Continuous drain current ( $T_A = 100^\circ C$ )		-1.4	A
Pulsed drain current <sup>1)</sup>	$I_{DM}$	-10	A
Gate-Source voltage	$V_{GSS}$	$\pm 12$	V
Power Dissipation ( $T_A = 25^\circ C$ )	$P_D$	0.78	W
Storage Temperature Range	$T_{STG}$	-55 to +150	°C
Operating Junction Temperature Range	$T_J$	-55 to +150	°C

### Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JA}$	160	°C/W

**Package Marking and Ordering Information**

Device	Device Package	Marking
LPSC2301	SOT-23	2301

**Electrical Characteristics**
 $T_J = 25^\circ\text{C}$  unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static characteristics</b>						
Drain-source breakdown voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0 \text{ V}, I_D=-250\mu\text{A}$	-20	---	---	V
Gate threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_D=-250\mu\text{A}$	-0.4	-0.75	-1	V
Drain-source leakage current	$I_{\text{DSS}}$	$V_{\text{DS}}=-20 \text{ V}, V_{\text{GS}}=0 \text{ V}, T_J = 25^\circ\text{C}$	---	---	-1	$\mu\text{A}$
		$V_{\text{DS}}=-16 \text{ V}, V_{\text{GS}}=0 \text{ V}, T_J = 125^\circ\text{C}$	---	---	-10	$\mu\text{A}$
Gate leakage current, Forward	$I_{\text{GSSF}}$	$V_{\text{GS}}=12 \text{ V}, V_{\text{DS}}=0 \text{ V}$	---	---	100	nA
Gate leakage current, Reverse	$I_{\text{GSSR}}$	$V_{\text{GS}}=-12 \text{ V}, V_{\text{DS}}=0 \text{ V}$	---	---	-100	nA
Drain-source on-state resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}}=-4.5 \text{ V}, I_D=-2 \text{ A}$	---	80	110	$\text{m}\Omega$
		$V_{\text{GS}}=-2.5 \text{ V}, I_D=-1.5 \text{ A}$	---	100	130	$\text{m}\Omega$
Forward transconductance	$g_{\text{fs}}$	$V_{\text{DS}} = -5 \text{ V}, I_D=2\text{A}$	---	6	---	S
<b>Dynamic characteristics</b>						
Input capacitance	$C_{\text{iss}}$	$V_{\text{DS}} = -10 \text{ V}, V_{\text{GS}} = 0 \text{ V}, F = 1\text{MHz}$	---	406	---	pF
Output capacitance	$C_{\text{oss}}$		---	51.7	---	
Reverse transfer capacitance	$C_{\text{rss}}$		---	44.1	---	
Turn-on delay time	$t_{\text{d(on)}}$	$V_{\text{DD}} = -10\text{V}, V_{\text{GS}}=-4.5\text{V}, I_D = -2\text{A}$	---	10	---	ns
Rise time	$t_r$		---	5.3	---	
Turn-off delay time	$t_{\text{d(off)}}$		---	32	---	
Fall time	$t_f$		---	8	---	
Gate resistance	$R_g$	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=0\text{V}, f=1\text{MHz}$	---	20	---	$\Omega$
<b>Gate charge characteristics</b>						
Gate to source charge	$Q_{\text{gs}}$	$V_{\text{DS}}=-10 \text{ V}, I_D=-2\text{A}, V_{\text{GS}}=-4.5 \text{ V}$	---	1.5	---	nC
Gate to drain charge	$Q_{\text{gd}}$		---	1.2	---	
Gate charge total	$Q_g$		---	8.2	---	
<b>Drain-Source diode characteristics and Maximum Ratings</b>						
Continuous Source Current	$I_s$	$V_{\text{GS}}=0\text{V}, I_s=-2\text{A}, T_J=25^\circ\text{C}$	---	---	-2	A
Pulsed Source Current <sup>2)</sup>	$I_{\text{SM}}$		---	---	-10	A
Diode Forward Voltage	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}, I_s=-2\text{A}, T_J=25^\circ\text{C}$	---	---	-1.2	V

Notes:

1: Repetitive Rating: Pulse width limited by maximum junction temperature.

2: Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

## Electrical Characteristics Diagrams

Figure 1. Typ. Output Characteristics

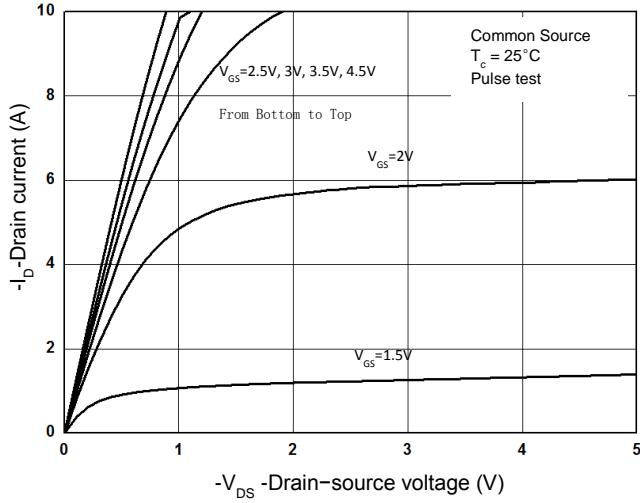


Figure 2. Transfer Characteristics

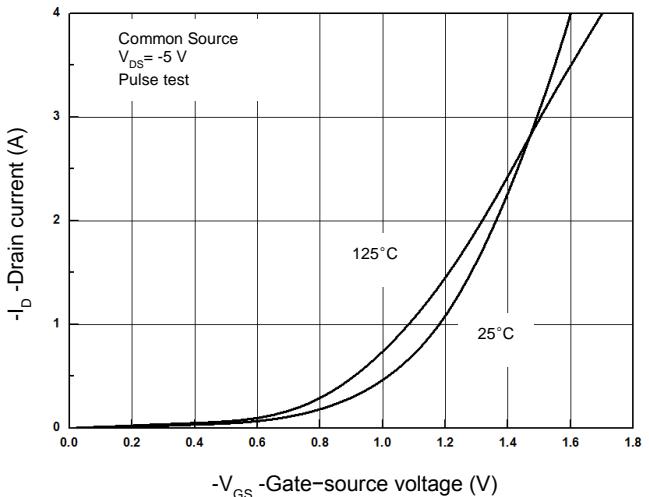


Figure 3. Capacitance Characteristics

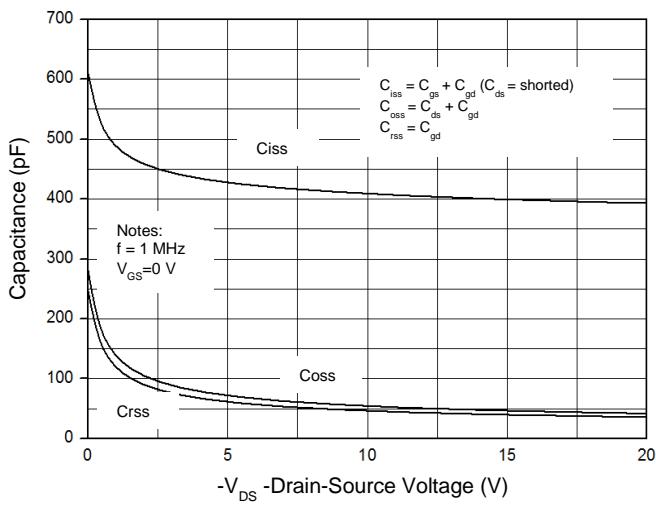


Figure 4. Gate Charge Waveform

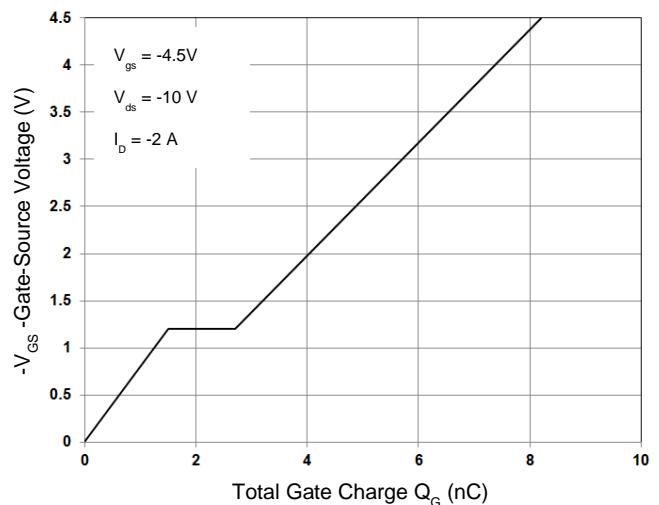


Figure 5. Body-Diode Characteristics

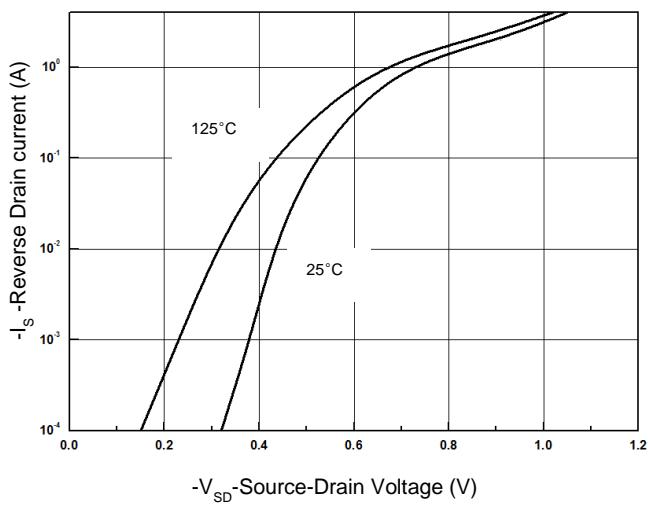


Figure 6. Rdson-Drain Current

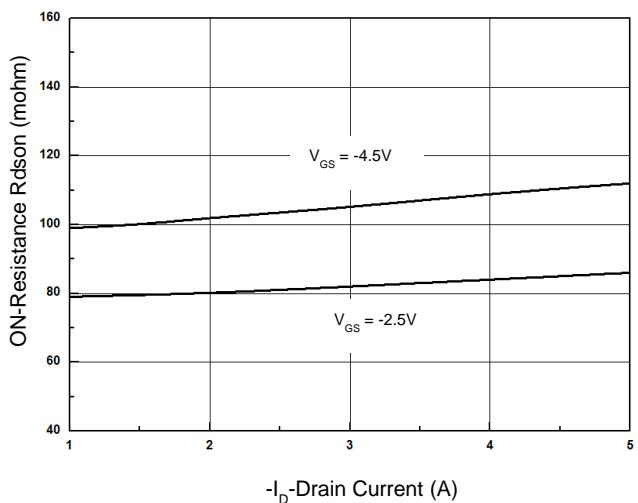


Figure 7. Rdson-Junction Temperature(°C)

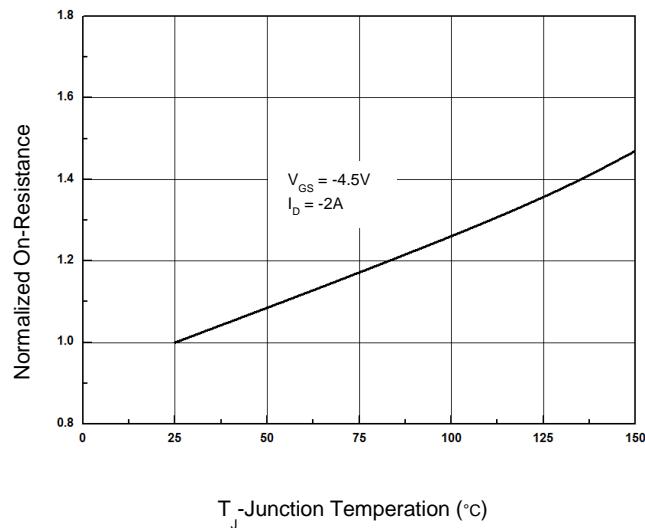


Figure 8. Maximum Safe Operating Area

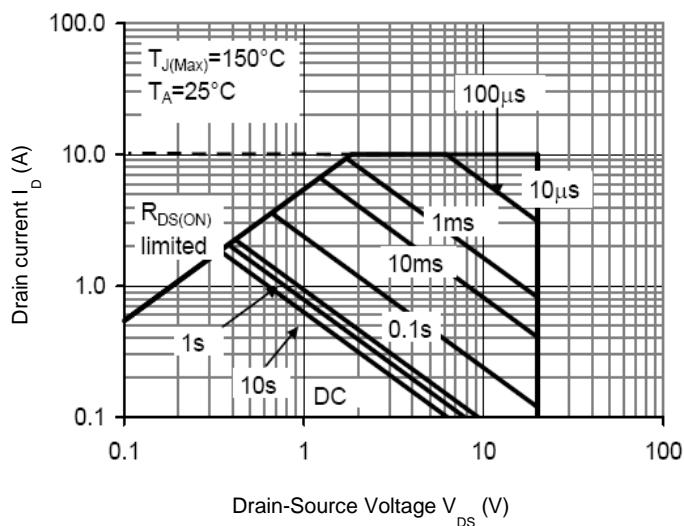
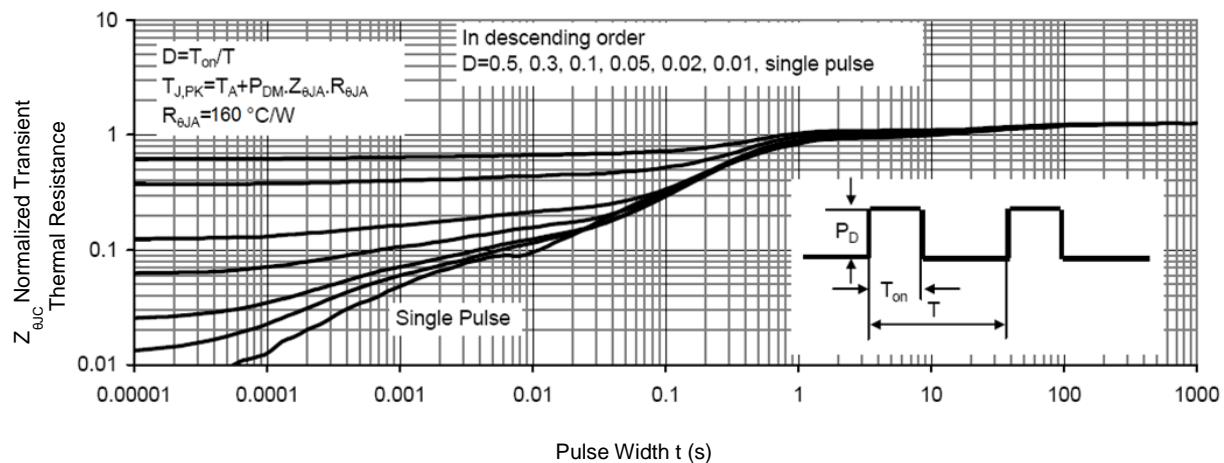


Figure 6. Normalized Maximum Transient Thermal Impedance (RthJA)



## Test Circuit & Waveform

Figure 8. Gate Charge Test Circuit & Waveform

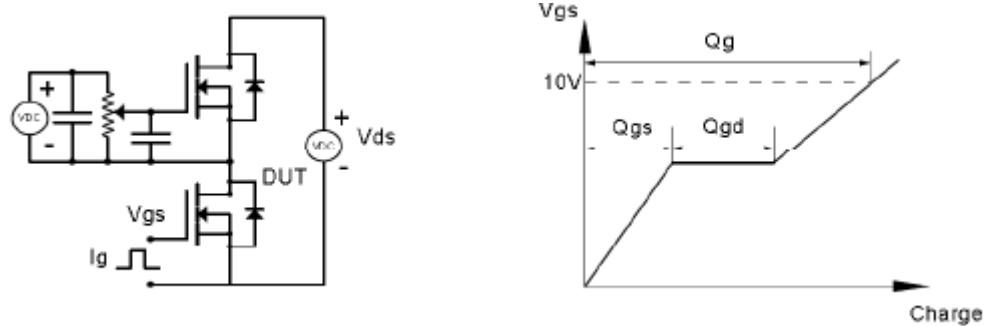


Figure 9. Resistive Switching Test Circuit & Waveforms

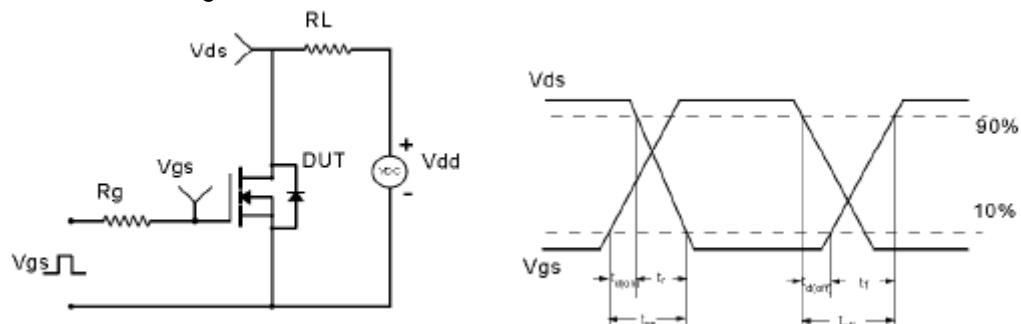


Figure 10. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

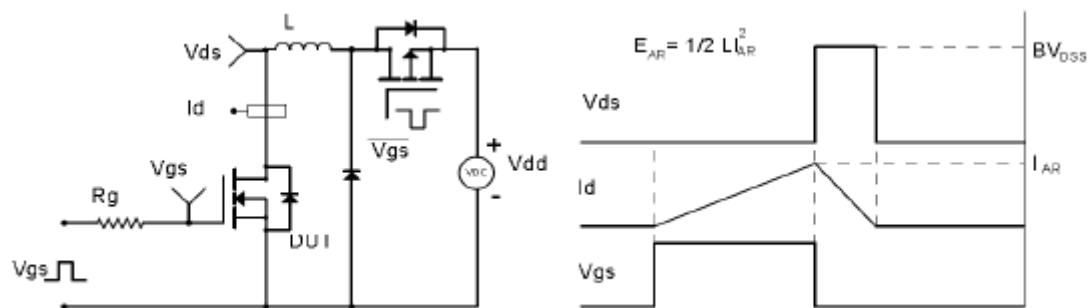
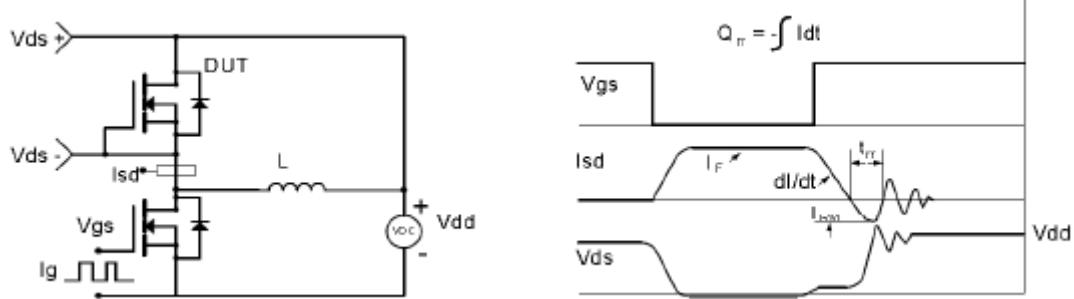
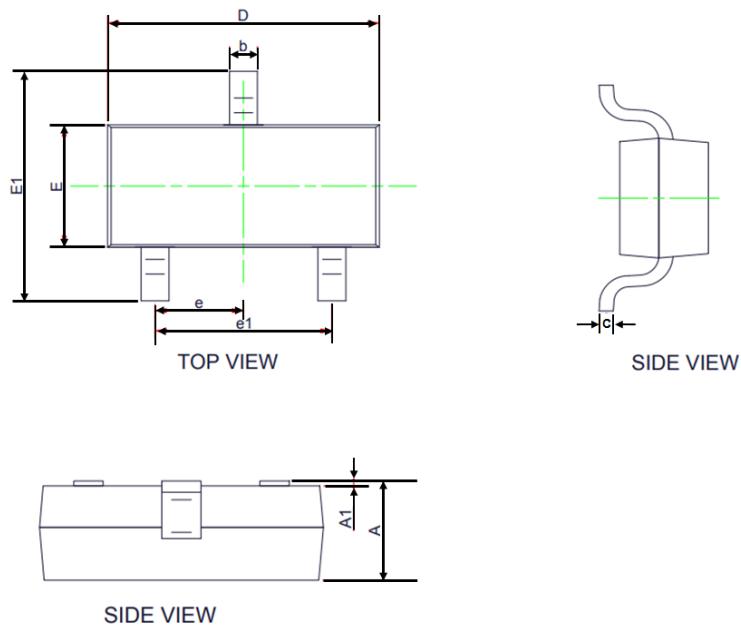


Figure 11. Diode Recovery Circuit & Waveform

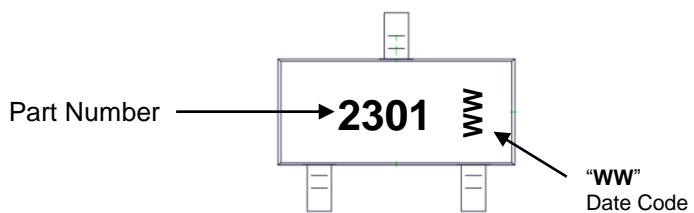


## Mechanical Dimensions for SOT-23



SYMBOL	COMMON DIMENSIONS			
	MILLIMETERS		INCHS	
	MIN	MAX	MIN	MAX
A	0.95	1.40	0.037	0.055
A1	0.01	0.10	0.000	0.004
b	0.35	0.50	0.014	0.020
c	0.08	0.19	0.003	0.007
D	2.70	3.10	0.106	0.122
E	1.20	1.65	0.047	0.065
E1	2.20	3.00	0.087	0.118
e	0.95 TYP.		0.037 TYP.	
e1	1.78	2.04	0.070	0.080

## SOT-23 Part Marking Information



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